VITELIC

V53C400
HIGH PERFORMANCE, LOW POWER 4M X 1 BIT FAST PAGE MODE CMOS DYNAMIC RAM

PRELIMINARY

HIGH PERFORMANCE V53C400	70/70L	80/80L	10/10L
Max. $\overline{RAS}$ Access Time, (t_{RAC})	70 ns	80 ns	100 ns
Max. Column Address Access Time, (t_{CAA})	35 ns	40 ns	50 ns
Min. Fast Page Mode Cycle Time, (t_{PC})	50 ns	55 ns	65 ns
Min. Read/Write Cycle Time, (t_{RC})	130 ns	150 ns	180 ns

LOW POWER V53C400L	70L	80L	10L
Max. CMOS Standby Current, (I_{DD6})	0.4 mA	0.4 mA	0.4 mA

Features

- 4M x 1-bit organization
- RAS access time: 70,80,100 ns
- Low power dissipation
  - V53C400-10
    - — Operating Current – 70 mA max.
    - — TTL Standby Current – 2.0 mA max.
- Low CMOS Standby Current
  - V53C400 – 1.0 mA max.
  - V53C400L – 0.4 mA max.
- Battery Back-up Mode (V53C400L Only)
- Read-Modify-Write, $\overline{RAS}$-Only Refresh, $\overline{CAS}$-Before-$\overline{RAS}$ Refresh capability
- Refresh Interval
  - V53C400 – 1024 cycles/16ms
  - V53C400L – 1024 cycles/64ms
- On-chip substrate bias generator
- Fast Page Mode for a sustained data rate greater than 20 MHz
- Available in 26/20 pin SOJ package (300 mil)

Description

The Vitelic V53C400 is a high speed 4,194,304x1 bit CMOS dynamic random access memory. Fabricated with Vitelic's VICMOS V technology, the V53C400 offers a combination of features: Fast Page Mode for high data bandwidth, fast usable speed, CMOS standby current and, on request, extended refresh for very low data retention power (V53C400L).

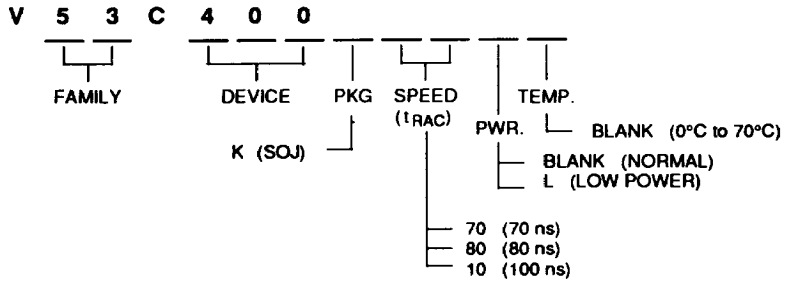
All inputs and outputs are TTL compatible. Input and output capacitances are significantly lowered to allow increased system performance. Fast Page Mode operation allows random access of up to 1024 bits within a row with cycle times as short as 50 ns. Because of static circuitry, the $\overline{CAS}$ clock is not in the critical timing path. The flow-through column address latches allow address pipelining while relaxing many critical system timing requirements for fast usable speed. These features make the V53C400 ideally suited for graphics, digital signal processing and high performance computing systems.

The V53C400L offers a maximum data retention power of 3.3 mW when operating in CMOS standby mode and performing $\overline{RAS}$-only or $\overline{CAS}$-before-$\overline{RAS}$ refresh cycles.

Device Usage Chart

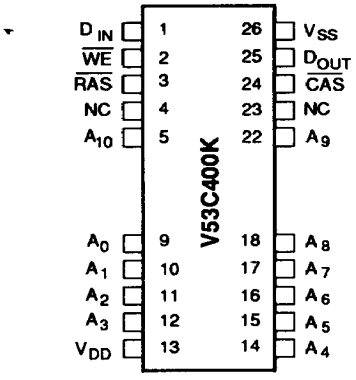
Operating Temperature Range	Package Outline	Access Time (ns)			Power		Temperature Mark
	K	70	80	100	Low	Std.	
0°C to 70 °C	•	•	•	•	•	•	Blank

V53C400 Rev. 01 September 1991

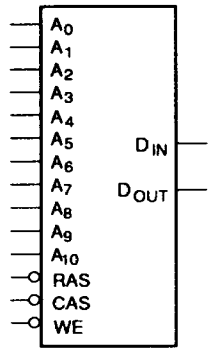


Description	Pkg.	Pin Count
SOJ	K	26/20

26/20 Lead SOJ Package PIN CONFIGURATION Top View



LOGIC SYMBOL



Pin Names

A_0–A_{10}	Address Inputs
$\overline{RAS}$	Row Address Strobe
$\overline{CAS}$	Column Address Strobe
$\overline{WE}$	Write Enable
D_{IN}	Data Input
D_{OUT}	Data Output
V_{DD}	+5V Supply
V_{SS}	0V Supply
NC	No Connect

Absolute Maximum Ratings*

Ambient Temperature
Under Bias ..... –10°C to +80°C
Storage Temperature (plastic) .... –55°C to +125°C
Voltage Relative to V_{SS} ..... –1.0 V to +7.0 V
Data Out Current ..... 50 mA
Power Dissipation ..... 1.0 W

*Note: Operation above Absolute Maximum Ratings can adversely affect device reliability.

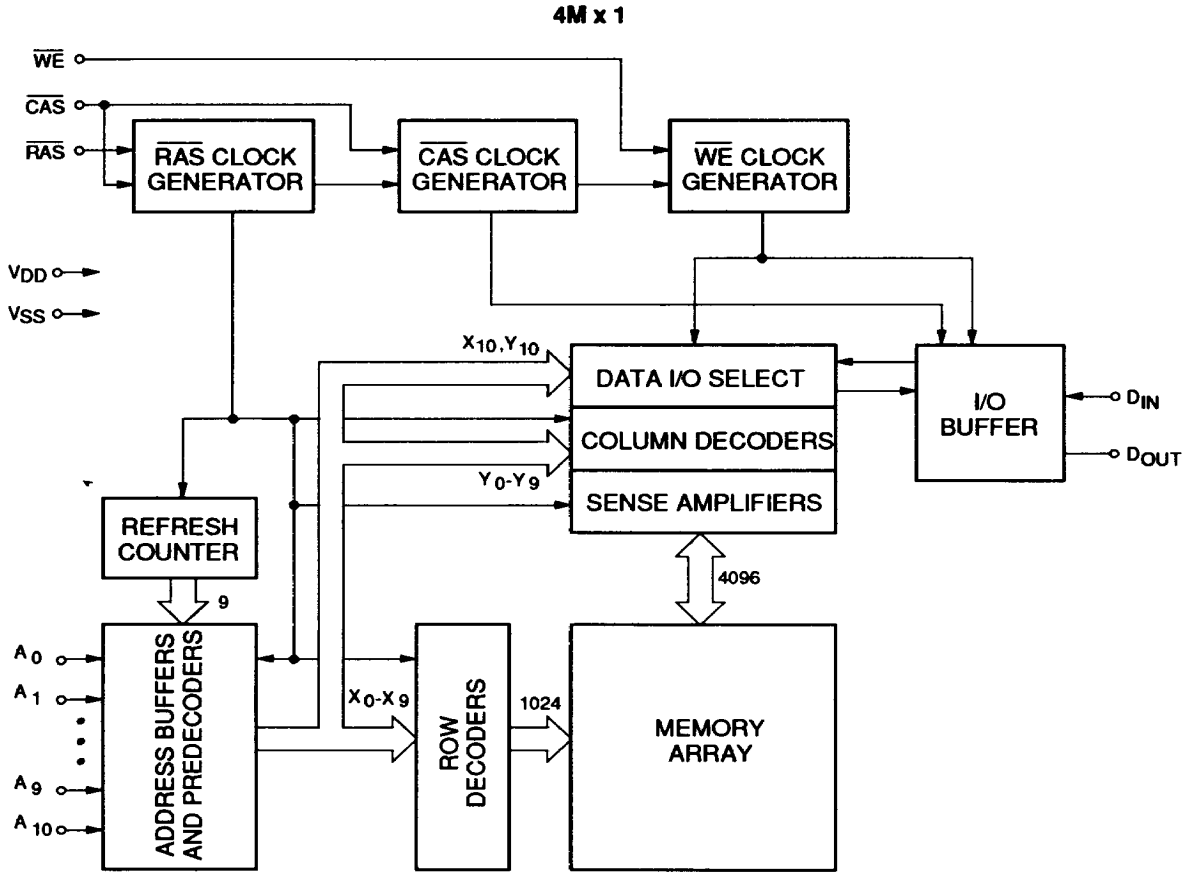
Capacitance*

T_A = 25°C, V_{DD} = 5 V ±10%, V_{SS} = 0 V

Symbol	Parameter	Typ.	Max.	Unit
C_{IN1}	Address	—	6	pF
C_{IN2}	$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$	—	7	pF
C_{OUT}	D_{IN}/D_{OUT}	—	7	pF

*Note: Capacitance is sampled and not 100% tested

Block Diagram



DC and Operating Characteristics (1-2)

T_A = 0°C to 70°C, V_{DD} = 5 V ± 10%, V_{SS} = 0 V, unless otherwise specified.

Symbol	Parameter	Access Time	V53C400		V53C400L		Unit	Test Conditions	Notes
			Min.	Max.	Min.	Max.			
I_{LI}	Input Leakage Current (any input pin)		−10	10	−10	10	µA	$V_{SS} \le V_{IN} \le V_{DD}$	
I_{LO}	Output Leakage Current (for High-Z State)		−10	10	−10	10	µA	$V_{SS} \le V_{OUT} \le V_{DD}$ $\overline{RAS}$, $\overline{CAS}$ at V_{IH}	
I_{DD1}	V_{DD} Supply Current, Operating	70		90		90	mA	$t_{RC} = t_{RC}$ (min.)	1, 2
		80		80		80			
		100		70		70			
I_{DD2}	V_{DD} Supply Current, TTL Standby			2.0		2.0	mA	$\overline{RAS}$, $\overline{CAS}$ at V_{IH} other inputs ≥ V_{SS}	
I_{DD3}	V_{DD} Supply Current, $\overline{RAS}$-Only Refresh	70		90		90	mA	$t_{RC} = t_{RC}$ (min.)	2
		80		80		80			
		100		70		70			
I_{DD4}	V_{DD} Supply Current, Fast Page Mode Operation	70		80		80	mA	Minimum Cycle	1, 2
		80		70		70			
		100		60		60			
I_{DD5}	V_{DD} Supply Current, Standby, Output Enabled			5		4	mA	$\overline{RAS}$=V_{IH}, $\overline{CAS}$=V_{IL} other inputs ≥ V_{SS}	
I_{DD6}	V_{DD} Supply Current, CMOS Standby			1		0.4	mA	$\overline{RAS} \ge V_{DD} - 0.2$ V $\overline{CAS} \ge V_{DD} - 0.2$V other inputs ≥ V_{SS}	
I_{DD7}	Battery Back-up Data Retention Current (Only V53C400L)			N.A.		0.6	mA	$\overline{CAS}$-Before-$\overline{RAS}$ Refresh cycle t_{RC} = 62.5 µs CMOS clock levels	18
V_{IL}	Input Low Voltage		−1.0	0.8	−1.0	0.8	V		3
V_{IH}	Input High Voltage		2.4	V_{DD}+1	2.4	V_{DD}+1	V		3
V_{OL}	Output Low Voltage			0.4		0.4	V	I_{OL} = 4.2 mA	
V_{OH}	Output High Voltage		2.4		2.4			I_{OH} = −5 mA	

AC Characteristics

T_A = 0°C to 70°C, V_{DD} = 5 V ±10%, V_{SS} = 0 V, unless otherwise noted

#	JEDEC Symbol	Symbol	Parameter	70/L		80/L		10/L		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.		
1	t_{RL1RH1}	t_{RAS}	$\overline{RAS}$ Pulse Width	70	75K	80	75K	100	75K	ns	
2	t_{RL2RL}	t_{RC}	Read or Write Cycle Time	130		150		180		ns	
3	t_{RH2RL2}	t_{RP}	$\overline{RAS}$ Precharge Time	50		60		70		ns	
4	t_{AVRL2}	t_{ASR}	Row Address Setup Time	0		0		0		ns	
5	t_{RL1AX}	t_{RAH}	Row Address Hold Time	10		10		15		ns	
6	t_{AVRH1}	t_{CAR}	Column Address to $\overline{RAS}$ Setup Time	35		40		50		ns	
7	t_{RL1AV}	t_{RAD}	$\overline{RAS}$ to Column Address Delay Time	15	35	15	40	20	50	ns	4
8	t_{AVCL2}	t_{ASC}	Column Address Setup Time	0		0		0		ns	
9	t_{CL1AX}	t_{CAH}	Column Address Hold Time	15		15		20		ns	
10	t_{RL1CL1}	t_{RCD}	$\overline{RAS}$ to $\overline{CAS}$ Delay	20	50	20	60	25	75	ns	5
11	t_{RL1QV}	t_{RAC}	Access Time from $\overline{RAS}$		70		80		100	ns	6,7,8
12	t_{AVQV}	t_{CAA}	Access Time from Column Address		35		40		50	ns	8,9,10
13	t_{CL1QV}	t_{CAC}	Access Time from $\overline{CAS}$		20		20		25	ns	8,10
14	$t_{CL1CH1(R)}$	$t_{CAS(R)}$	$\overline{CAS}$ Pulse Width in Read Cycle	20		20		25		ns	
15	$t_{CL1RH1(R)}$	$t_{RSH(R)}$	$\overline{RAS}$ Hold Time (Read Cycle)	20		20		25		ns	
16	t_{WH2CL2}	t_{RCS}	Read Command Setup Time	0		0		0		ns	
17	t_{CH2WX}	t_{RCH}	Read Command Hold Time Referenced to $\overline{CAS}$	0		0		0		ns	11
18	t_{RH2WX}	t_{RRH}	Read Command Hold Time Referenced to $\overline{RAS}$	0		0		0		ns	11
19	t_{CH2RL2}	t_{CRP}	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	5		5		10		ns	
20	t_{CH2QX}	t_{OFF}	Output Buffer Turn Off Delay	0	15	0	20	0	25	ns	12

AC Characteristics (Cont'd.)

#	JEDEC Symbol	Symbol	Parameter	70/L		80/L		10/L		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.		
21	t_{CH2QV}	t_{OH}	Data Hold Time from $\overline{CAS}$	0		0		0		ns	11
22	t_{WL1WH1}	t_{WP}	Write Pulse Width	10		15		20		ns	
23	t_{CH2CL2}	t_{CP}	$\overline{CAS}$ Precharge Time	10		10		10		ns	
24	t_{RL1AX}	t_{AR}	Column Address Hold Time from $\overline{RAS}$	55		60		75		ns	
25	$t_{CL1CH1(W)}$	$t_{CAS(W)}$	$\overline{CAS}$ Pulse Width in Write Cycle	20		20		25		ns	
26	$t_{CL1RH1(W)}$	$t_{RSH(W)}$	$\overline{RAS}$ or $\overline{CAS}$ Hold Time in Write Cycle	20		20		25		ns	
27	t_{RL1WH1}	t_{WCR}	Write Command Hold Time from $\overline{RAS}$	55		60		75		ns	
28	t_{WL1CL2}	t_{WCS}	Write Command Setup Time	0		0		0		ns	13,14
29	t_{CL1WH1}	t_{WCH}	Write Command Hold Time	10		15		20		ns	
30	t_{DVWL2}	t_{DS}	Data In Setup Time	0		0		0		ns	15
31	t_{WH1DX}	t_{DH}	Data In Hold Time	15		15		20		ns	15
32	t_{RL1DX}	t_{DHR}	Data In Hold Time Referenced to $\overline{RAS}$	55		60		75		ns	
33	t_{RL2RL2} (RMW)	t_{RWC}	Read-Modify-Write Cycle Time	155		175		210		ns	
34	t_{RL1RH1} (RMW)	t_{RRW}	Read-Modify-Write Cycle $\overline{RAS}$ Pulse Width	95		105		130		ns	
35	t_{RL1WL2}	t_{RWD}	$\overline{RAS}$ to $\overline{WE}$ Delay Time Read-Modify-Write Cycle	70		80		100		ns	13
36	t_{CL1WL2}	t_{CWD}	$\overline{CAS}$ to $\overline{WE}$ Delay	20		20		25		ns	13
37	t_{AVWL2}	t_{AWD}	Column Address to $\overline{WE}$ Delay	35		40		50		ns	13
38	t_{CH2QV}	t_{CAP}	Access Time from Column Precharge		40		45		55	ns	17
39	$t_{CL2CL2(R)}$	t_{PC}	Fast Page Mode Read or Write Cycle Time	50		55		65		ns	

AC Characteristics (Cont'd.)

#	JEDEC Symbol	Symbol	Parameter	70/L		80/L		10/L		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.		
40	t_{CL2CL2}	t_{PCM} (RMW)	Fast Page Mode Read-Modify-Write Cycle Time	75		80		95		ns	
41	t_{WL1RH1}	t_{RWL}	Write Command to $\overline{RAS}$ Lead Time	20		20		25		ns	
42	t_{WL1CH1}	t_{CWL}	Write Command to $\overline{CAS}$ Lead Time	20		20		25		ns	
43	t_{RH2CL2}	t_{RPC}	$\overline{RAS}$ to $\overline{CAS}$ Precharge Time	5		5		5		ns	
44	t_{CL1RL2}	t_{CSR}	$\overline{CAS}$ Setup Time $\overline{CAS}$-before-$\overline{RAS}$ Refresh	5		5		5		ns	
45	t_{RL1CH1}	t_{CHR}	$\overline{CAS}$ Hold Time $\overline{CAS}$-before-$\overline{RAS}$ Cycle	15		15		15		ns	
46	t_{RL1CH1}	t_{CSH}	$\overline{CAS}$ Hold Time	70		80		100		ns	
47	t_{WH2RL2}	t_{WRP}	$\overline{WE}$ to $\overline{RAS}$ precharge time ($\overline{CAS}$-Before-$\overline{RAS}$ Refresh cycle)	10		10		10		ns	
48	t_{RL1WL2}	t_{WRH}	$\overline{WE}$ Hold Time from $\overline{RAS}$ ($\overline{CAS}$-Before-$\overline{RAS}$ Refresh Cycle)	10		10		10		ns	
49	t_{WL1RL2}	t_{WSR}	$\overline{RAS}$ to $\overline{WE}$ set-up Time (Test Mode)	10		10		10		ns	20, 21
50	t_{RL1WH1}	t_{WHR}	$\overline{RAS}$ to $\overline{WE}$ hold Time (Test Mode)	10		10		10		ns	20, 21
51	t_T	t_T	Transition Time (Rise and Fall)	3	50	3	50	3	50	ns	16
52		t_{REF}	Refresh Interval (1024 Cycles)		16		16		16	ms	19
53		t_{REF}	Refresh Interval V53C400L Only (1024 Cycles, t_{RC} = 62.5 µs)		64		64		64	ms	18,19

Notes:

1. I_{DD} is dependent on output loading when the device output is selected. Specified I_{DD} (max.) is measured with the output open.
2. I_{DD} is dependent upon the number of address transitions. Specified I_{DD} (max.) is measured with a maximum of two transitions per address cycle in Fast Page Mode.
3. Specified V_{IL} (min.) is steady state operating. During transitions, V_{IL} (min.) may undershoot to –1.0 V for a period not to exceed 20 ns. All AC parameters are measured with V_{IL} (min.) ≥ V_{SS} and V_{IH} (max.) ≤ V_{DD}.
4. Operation within the t_{RAD} (max.) limit ensures that t_{RAC} (max.) can be met. t_{RAD} (max.) is specified as a reference point only. If t_{RAD} is greater than the specified t_{RAD} (max.) limit, the access time is controlled by t_{CAA} and t_{CAC}.
5. t_{RCD} (max.) is specified for reference only. Operation within t_{RCD} (max.) limits insures that t_{RAC} (max.) and t_{CAA} (max.) can be met. If t_{RCD} is greater than the specified t_{RCD} (max.), the access time is controlled by t_{CAA} and t_{CAC}.
6. Assumes that $t_{RAD} \leq t_{RAD}$ (max.). If t_{RAD} is greater than t_{RAD} (max.), t_{RAC} will increase by the amount that t_{RAD} exceeds t_{RAD} (max.).
7. Assumes that $t_{RCD} \leq t_{RCD}$ (max.). If t_{RCD} is greater than t_{RCD} (max.), t_{RAC} will increase by the amount that t_{RCD} exceeds t_{RCD} (max.).
8. Measured with a load equivalent to two TTL inputs and 100 pF.
9. Assumes that $t_{RAD} \geq t_{RAD}$ (max.).
10. Access time is determined by the longest of t_{CAA}, t_{CAC} and t_{CAP}.
11. Either t_{RRH} or t_{RCH} must be satisified for a Read Cycle to occur.
12. t_{OFF} and t_{ON} define the time at which D_{OUT} reaches an open circuit condition and are not referenced to the output voltage level.
13. t_{WCS}, t_{RWD}, t_{AWD} and t_{CWD} are not restrictive operating parameters.
14. t_{WCS} (min.) must be satisfied in an Early Write Cycle.
15. t_{DS} and t_{DH} are referenced to the latter occurrence of $\overline{CAS}$ or $\overline{WE}$.
16. t_T is measured between V_{IH} (min.) and V_{IL} (max.). AC-measurements assume t_T = 5 ns.
17. Assumes a three-state test load (5 pF and a 380 Ohm Thevenin equivalent).
18. An initial 200 µs pause and 8 $\overline{RAS}$-containing cycles are required when exiting an extended period of bias without clocks. An extended period of time without clocks is defined as one that exceeds the specified Refresh Interval.
19. This is battery backup data retention mode under $\overline{CAS}$-before-$\overline{RAS}$ refresh cycles.

    t_{RC} = 62.5 µs (62.5 µs x 1024 = 64 ms)

    $t_{RAS} = t_{RAS}$ (min) to 1 µs

    Input voltages : $\overline{RAS}$ and $\overline{CAS}$ $V_{IH} > V_{DD} - 0.2$ V

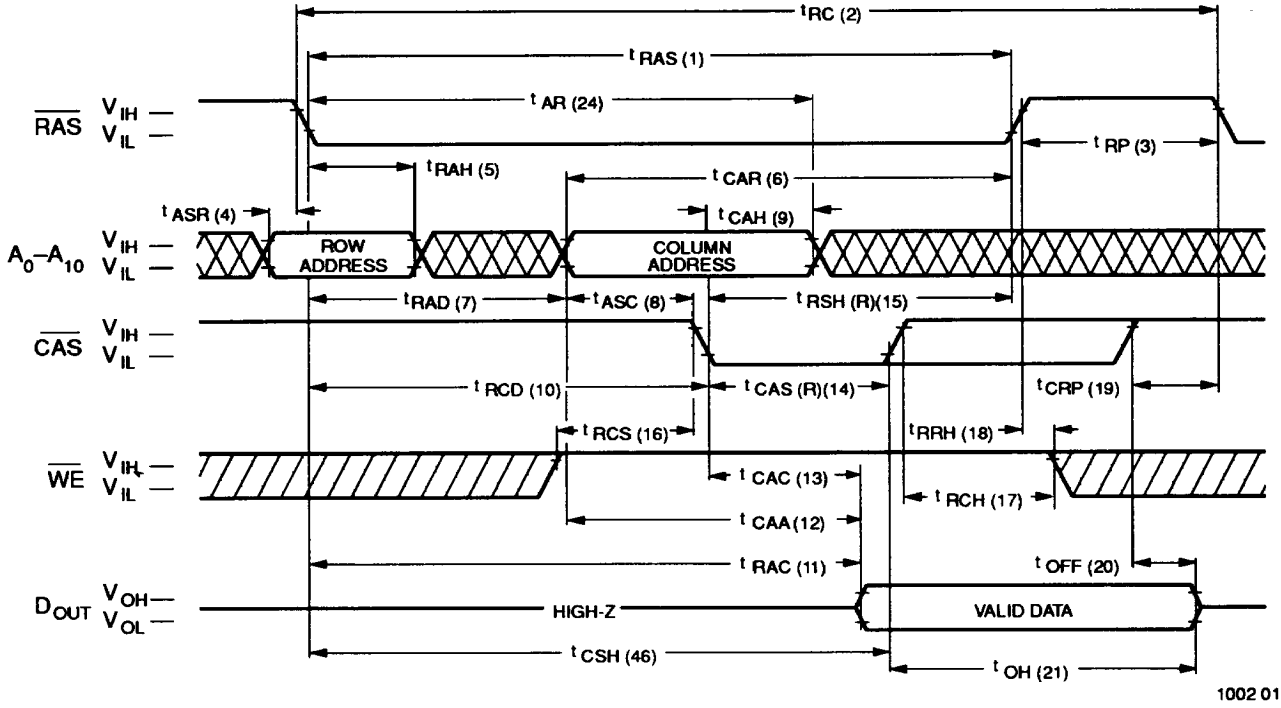
    $V_{IL} < 0.2$ V

    $\overline{WE}$ and $\overline{OE}$ $V_{IN} > V_{DD} - 0.2$ V

    All other inputs at stable V_{IH} or V_{IL}
20. The test mode is initiated by performing a $\overline{WE}$ and $\overline{CAS}$-before-$\overline{RAS}$ cycle. This mode is latched and remains in effect until the exit cycle is generated. The test mode specified in this data sheet is 8-bits parallel testing function.

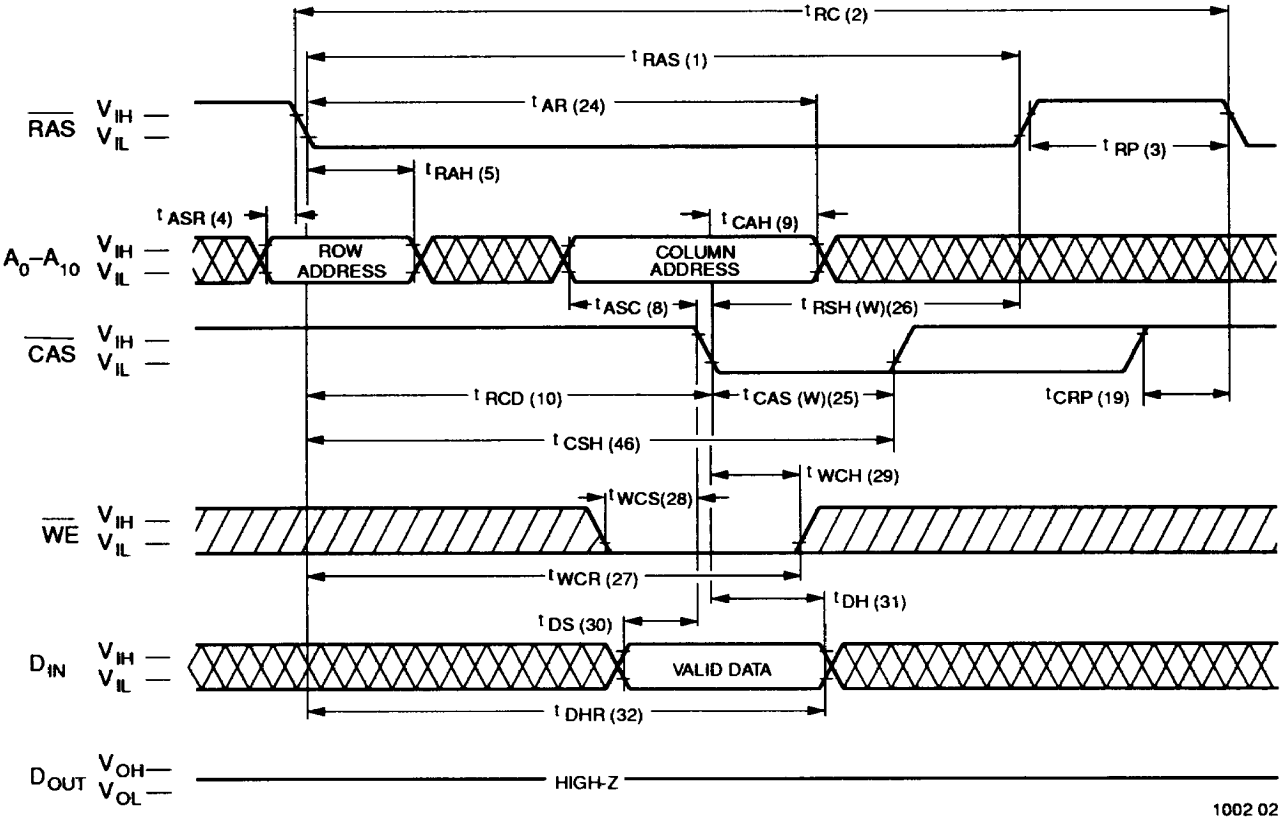
    RA_{10}, CA_{10}, CA_0 are not used. In the read cycle, if two internal bits on one I/O pin are equal, the I/O pin will indicate a high level. If internal bits on one I/O are not equal, then the I/O pin will indicate a low level. The test mode is cleared and the memory device returned to its normal operational state by performing a $\overline{RAS}$-only refresh cycle or a $\overline{CAS}$-before-$\overline{RAS}$ refresh cycle.
21. In a test mode read cycle, the value of access time parameters is delayed by 5 ns for the specified value. These parameters should be specified in test mode cycles by adding the above value (5 ns) to the specified value in this data sheet.

Waveforms of Read Cycle



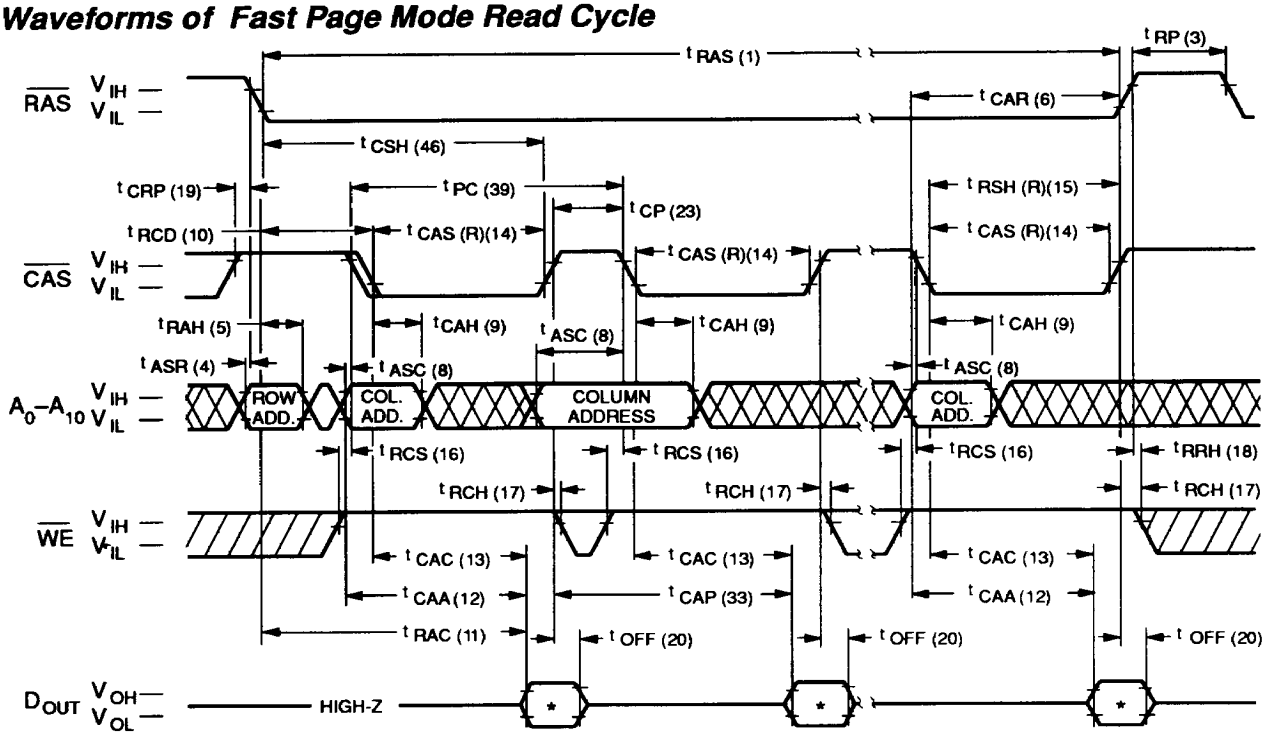
1002 01

Waveforms of Early Write Cycle



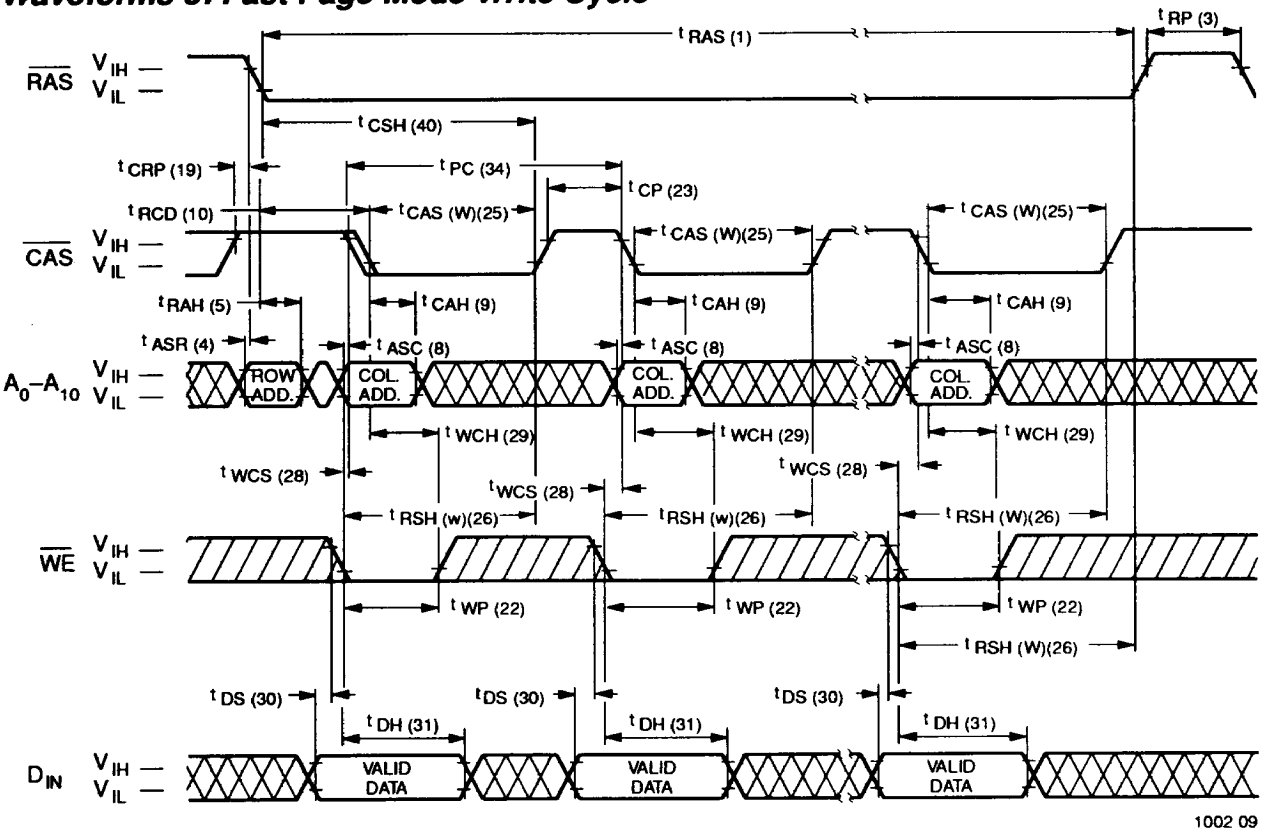
1002 02

Waveforms of Fast Page Mode Read Cycle

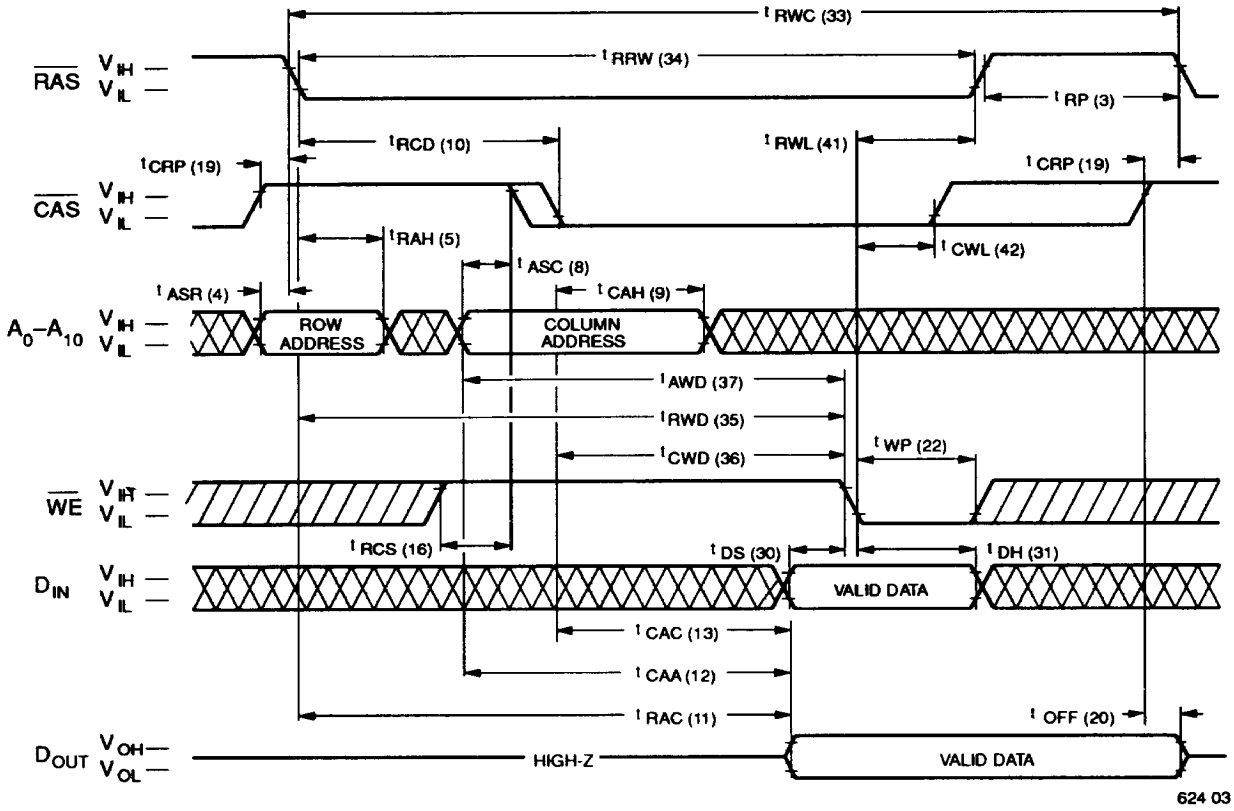


* Valid Data

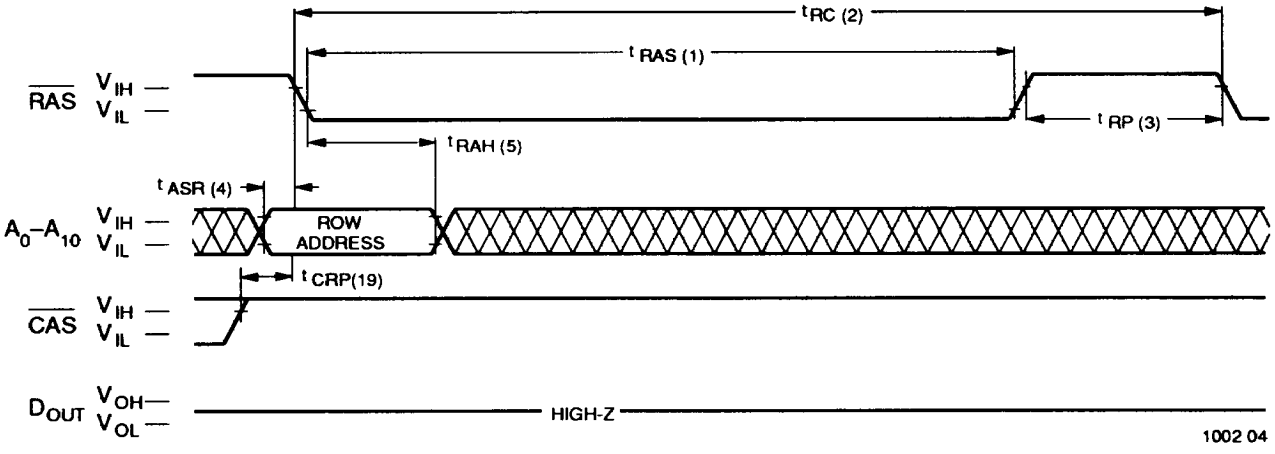
Waveforms of Fast Page Mode Write Cycle



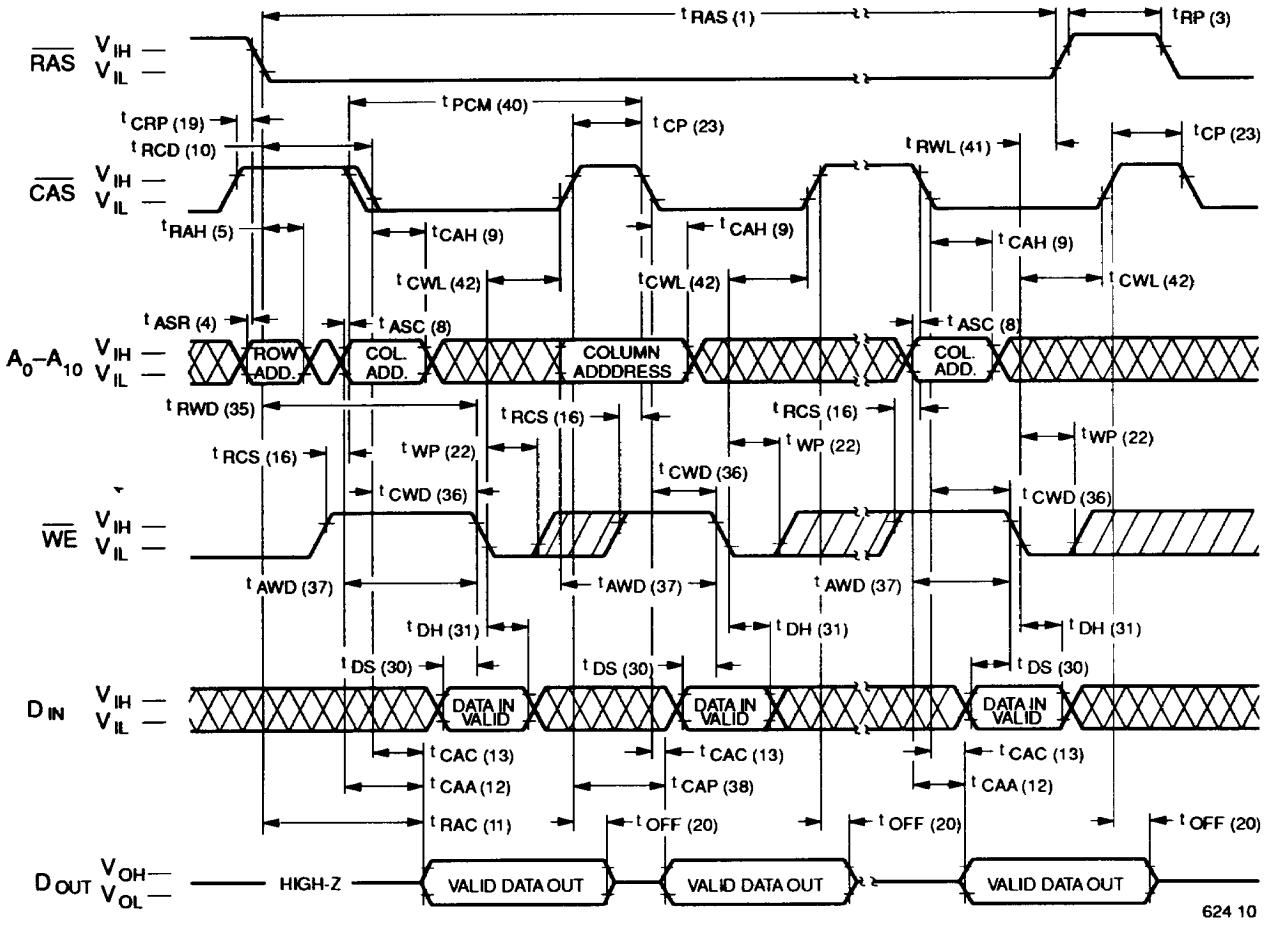
Waveforms of Read-Modify-Write Cycle



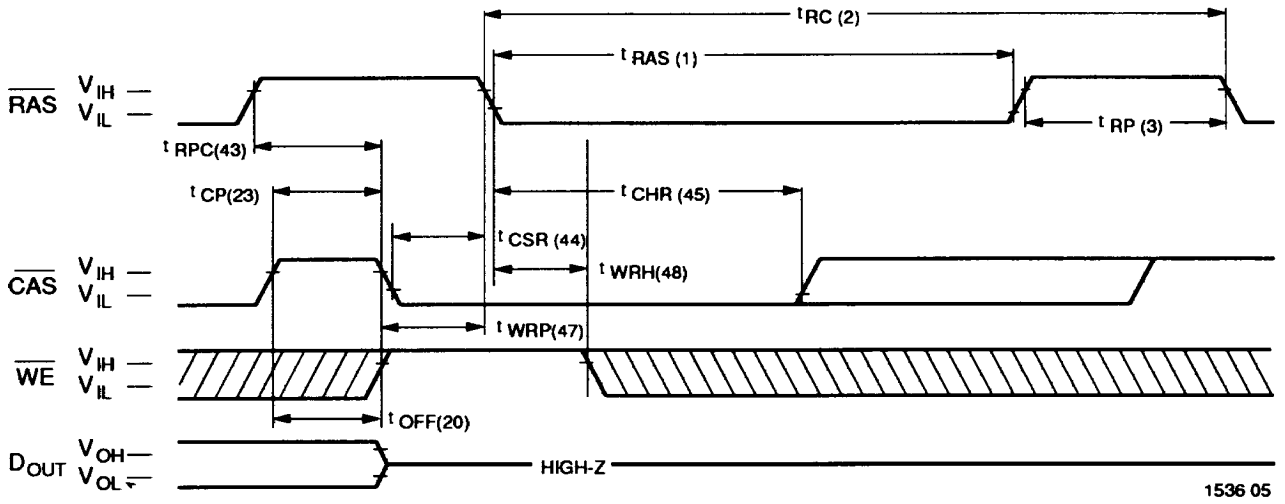
Waveforms of $\overline{RAS}$-Only Refresh Cycle



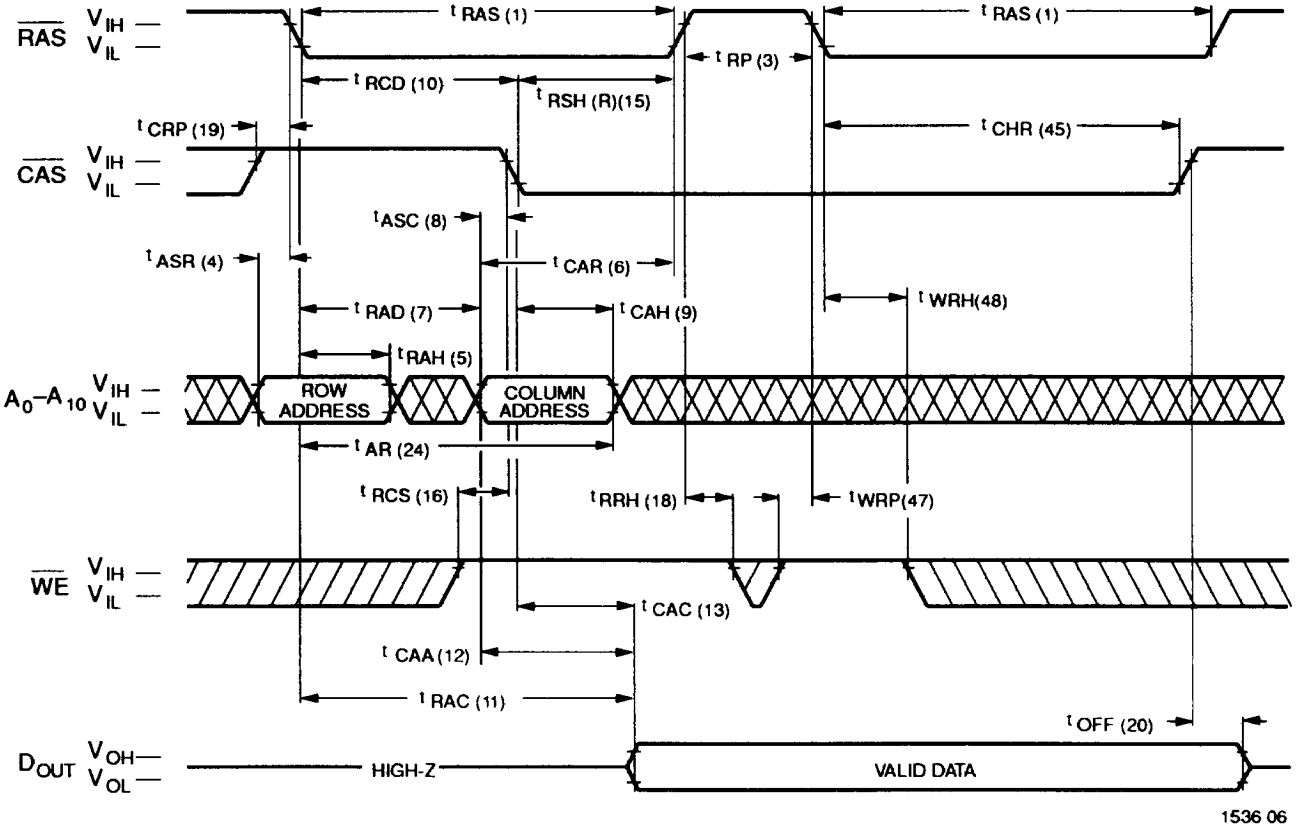
Waveforms of Fast Page Mode Read-Modify-Write Cycle



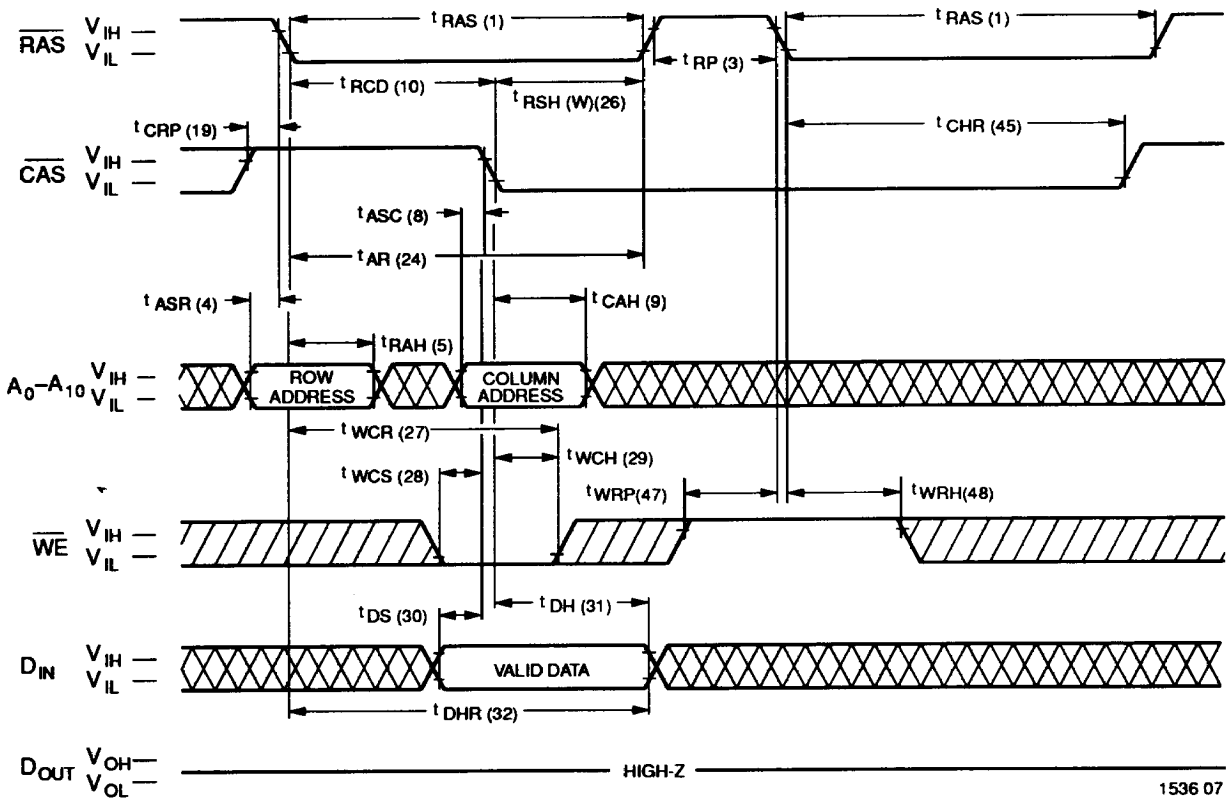
Waveforms of $\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle



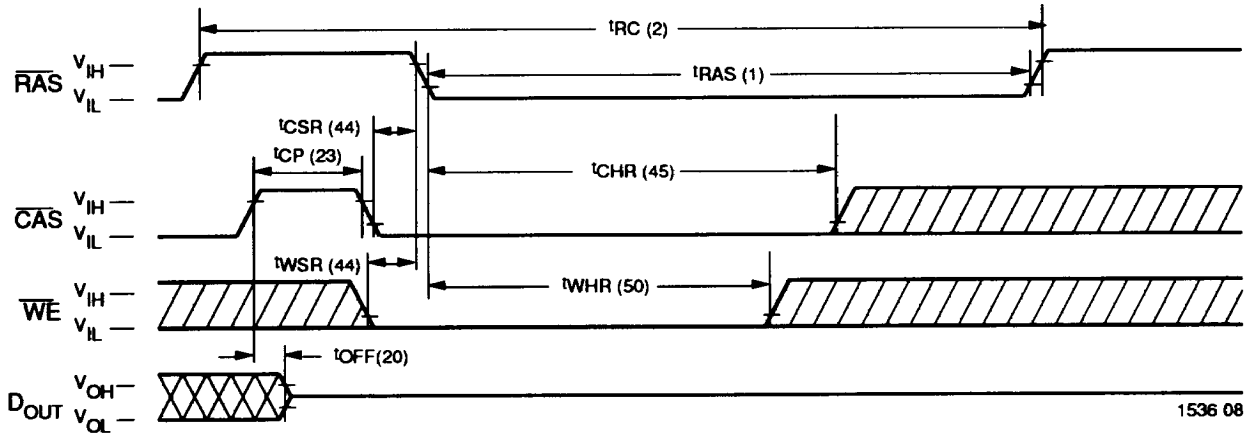
Waveforms of Hidden Refresh Cycle (Read)



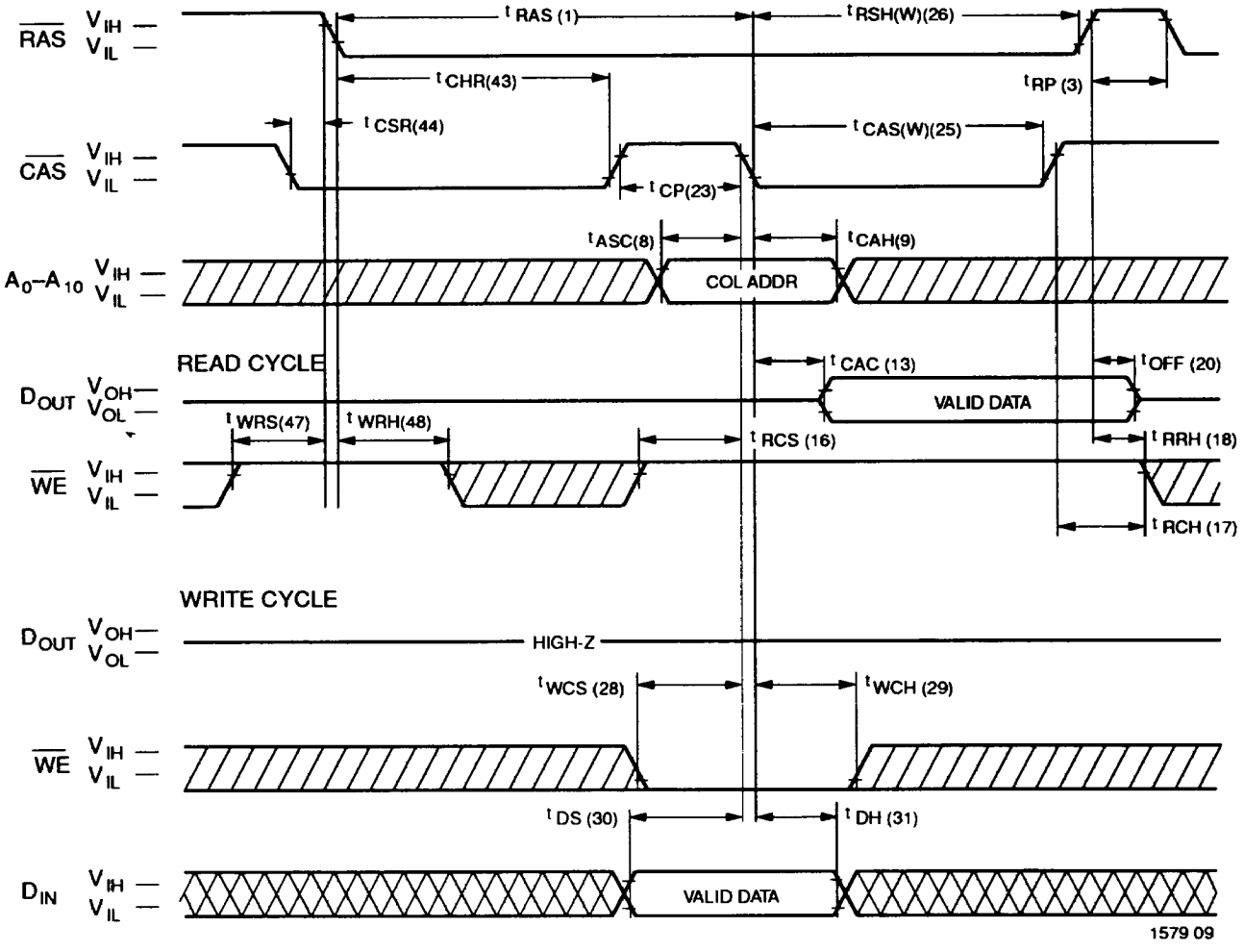
Waveforms of Hidden Refresh Cycle (Write)



Test Mode Initiation Cycle



Waveforms of $\overline{CAS}$-Before-$\overline{RAS}$ Refresh Counter Test Cycle



Functional Description

The V53C400 is a CMOS dynamic RAM optimized for high data bandwidth, low power applications. It is functionally similar to a traditional dynamic RAM. The V53C400 reads and writes data by multiplexing a 22-bit address into an 11-bit row and an 11-bit column address. The row address is latched by the Row Address Strobe ($\overline{RAS}$). The column address flows through an internal address buffer and is latched by the Column Address Strobe ($\overline{CAS}$). Because access time is primarily dependent on a valid column address rather than the precise time that the $\overline{CAS}$ edge occurs, the delay from $\overline{RAS}$ to $\overline{CAS}$ has little effect on the access time.

Memory Cycle

A memory cycle is initiated by bringing $\overline{RAS}$ low. Any memory cycle, once initiated, must not be ended or aborted before the minimum t_{RAS} time has expired. This ensures proper device operation and data integrity. A new cycle must not be initiated until the minimum precharge time t_{RP}/t_{CP} has elapsed.

Read Cycle

A Read cycle is performed by holding the Write Enable ($\overline{WE}$) signal high during a $\overline{RAS}/\overline{CAS}$ operation. The column address must be held for a minimum time specified by t_{AR}. Data Out becomes valid only when t_{RAC}, t_{CAA} and t_{CAC} are all satisfied. As a result, the access time is dependent on the timing relationships between t_{RAC}, t_{CAA} and t_{CAC}. For example, the access time is limited by t_{CAA} when t_{RAC} (min.) and t_{CAC} (min.) are both satisfied.

Write Cycle

A Write cycle is performed by taking $\overline{WE}$ and $\overline{CAS}$ low during a $\overline{RAS}$ operation. The column address is latched by $\overline{CAS}$. The write can be $\overline{WE}$ controlled or $\overline{CAS}$ controlled depending on whether $\overline{WE}$ or $\overline{CAS}$ falls later. Consequently, the input data must be valid at or before the falling edge of $\overline{WE}$ or $\overline{CAS}$, whichever occurs last. In a $\overline{CAS}$-controlled Write Cycle when the leading edge of $\overline{WE}$ occurs prior to the $\overline{CAS}$ low transition, the output (D_{OUT}) pin will be in the High-Z state at the beginning of the Write function. Ending the Write with $\overline{RAS}$ or $\overline{CAS}$ will maintain the output in the High-Z state.

Refresh Cycle

To retain data, 1024 Refresh Cycles are required in each 16 ms period. There are two ways to Refresh the memory:

1. By selecting all 1024 address combinations of A0 through A9 each 16 ms, a refresh of all rows is completed. Any Read, Write, Read-Modify-Write or $\overline{RAS}$-only cycle refreshes the addressed row.

2. Using a $\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle. If $\overline{CAS}$ makes a transition from low to high to low after the previous cycle and before $\overline{RAS}$ falls, $\overline{CAS}$-before-$\overline{RAS}$ refresh is activated. The V53C400 will use the output of an internal 10-bit counter as the source of row addresses and ignore external address inputs.

$\overline{CAS}$-before-$\overline{RAS}$ is a "refresh-only" mode and no data access or device selection is allowed. Thus, D_{OUT} will remain in the High-Z state during the cycle.

A $\overline{CAS}$-before-$\overline{RAS}$ counter test mode is provided to ensure reliable operation of the internal refresh counter. The user can use the counter test mode to write consecutive data patterns (1024 Write cycles) and then verify the written data by applying 1024 consecutive Read cycles. In this mode, the V53C400 ignores external row/column addresses and takes the output from the internal counter instead.

Data Retention Mode

The V53C400 offers a CMOS standby mode that is entered by causing the $\overline{RAS}$ clock to swing between a valid V_{IL} and an "extra high" V_{IH} within 0.2 V of V_{DD}. While the $\overline{RAS}$ clock is at the "extra high" level, the V53C400 power consumption is reduced to the low I_{DD6} level. Overall I_{DD} consumption when operating in this mode can be calculated as follows:

$$I = \frac{(t_{RC}) \times (I_{DD1}) + (t_{RX} - t_{RC}) \times (I_{DD6})}{t_{RX}}$$

Where t_{RC} = Refresh Cycle Time
t_{RX} = Refresh Interval / 1024

Fast Page Mode Operation

Fast Page Mode operation permits all 2048 columns within a selected row of the device to be randomly accessed at a high data rate. Maintaining $\overline{RAS}$ low while performing successive $\overline{CAS}$ cycles retains the row address internally and eliminates the need to reapply it for each cycle. The column address buffer acts as a transparent or flow-through latch while $\overline{CAS}$ is high.

Thus, access begins at the occurance of a valid column address rather than at the falling edge of $\overline{CAS}$, eliminating t_{ASC} and t_T from the critical timing path. $\overline{CAS}$ latches the address into the column address buffer and acts as on output enable.

During Fast Page Mode operation, Read, Write, Read-Modify-Write, or Read-Write-Read cycles are possible at random addresses within a row. Following the initial entry cycle into Fast Page Mode, access is t_{CAA} or t_{CAP} controlled. If the column address is valid prior to the rising edge of $\overline{CAS}$, the access time is determined by the by the $\overline{CAS}$ rising edge. If the column address is valid after the rising edge of $\overline{CAS}$, the access is timed from the occurrance of the valid address and is specified by t_{CAA}. In both cases, the falling edge of $\overline{CAS}$ latches the address and enables the output.

Fast Page Mode provides a sustained data rate of over 20 MHz for applications that require high data rates like bit-mapped graphics or high-speed signal processing. The following equation can be used to calculate the data rate:

$$\text{Data Rate} = \frac{2{,}048}{t_{RC} + 2{,}047 \times t_{PC}}$$

Data Output Operation

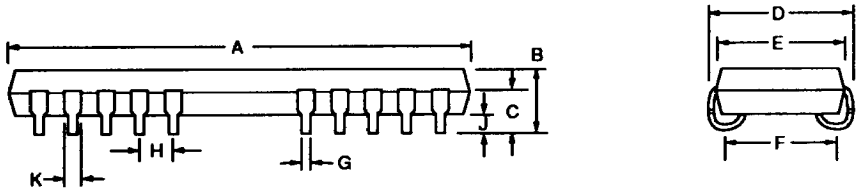
The V53C400 Data Output pin (D_{OUT}) has a three-state capability and is controlled by $\overline{CAS}$. When $\overline{CAS}$ is high($\geq V_{IH}$), the output is in the High-Z state. Table 1 summarizes the D_{OUT} states possible for various memory cycles.

Power On

After application of the V_{DD} an initial pause of 200 µs is required followed by a minimum of 8 initialization cycles (any combination of cycles containing a $\overline{RAS}$ clock). Eight initialization cycles are required after extended periods of bias without clocks (greater than the Refresh Interval). During power on, the V_{DD} current requirement of the V53C400 is dependent on the input levels of $\overline{RAS}$ and $\overline{CAS}$. If $\overline{RAS}$ is Low during power on, the device will go into an active cycle and I_{DD} will exhibit current transients. It is recommended that $\overline{RAS}$ and $\overline{CAS}$ track with V_{DD} or be held at a valid V_{IH} during power on to avoid current surges.

Table 1. Vitelic V53C400 Data Output
Operation for Various Cycle Types

Cycle Type	D_{OUT} State
Read Cycles	Data from Addressed Memory Cell
$\overline{CAS}$-Controlled Write Cycle (Early Write)	High-Z
$\overline{WE}$-Controlled Write Cycle (Late Write)	Active, not valid
Read-Modify-Write Cycles	Data from Addressed Memory Cell
Fast Page Mode Read Cycle	Data from Addressed Memory Cell
Fast Page Mode Write Cycle (Early Write)	High-Z
Fast Page Mode Read-Modify-Write Cycle	Data from Addressed Memory Cell
$\overline{RAS}$-only Refresh	High-Z
$\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle	Data remains as in previous cycle
$\overline{CAS}$-only Cycles	High-Z



26/20-pin SOJ

Dimension	Inches	Millimeters
A	0.672/0.684	17.069/17.374
B	0.125/0.135	3.175/3.429
C	0.082/0.093	2.083/2.362
D	0.332/0.342	8.433/8.687
E	0.296/0.304	7.518/7.722
F	0.255/0.275	6.477/6.985
G	0.018 Typ.	0.457 Typ.
H	0.05 Typ.	1.270 Typ.
J	0.026 Min.	0.660 Min.
K	0.028 Typ.	0.711 Typ.

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Printed in U.S.A.